



Plastic-Encapsulate Transistors

DUAL TRANSISTOR(NPN+NPN)

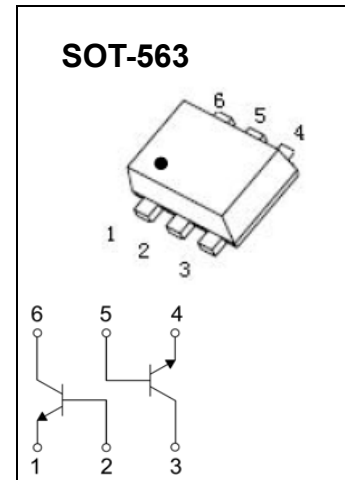
FEATURES

- Two 2SC2412K chips in a SOT-563 package
- Mounting possible with SOT-563 automatic mounting machines
- Transistor elements are independent, eliminating interference
- Mounting cost and area can be cut in half

MARKING:X1

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	150	mW
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}, I_C=1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.4	V
Transition frequency	f_T	$V_{CE}=12\text{V}, I_C=2\text{mA}, f=100\text{MHz}$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=12\text{V}, I_E=0, f=1\text{MHz}$		2.0	3.5	pF



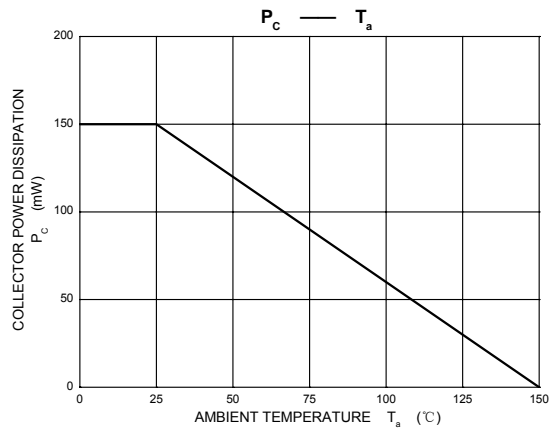
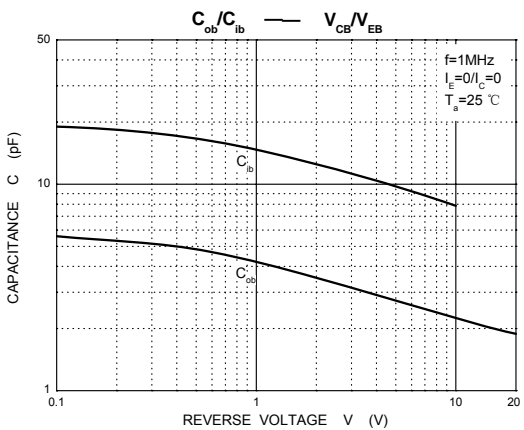
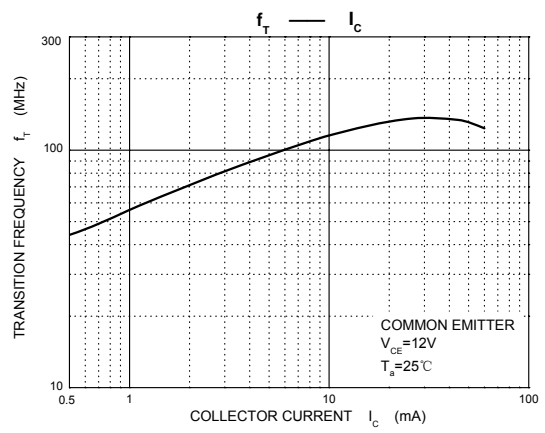
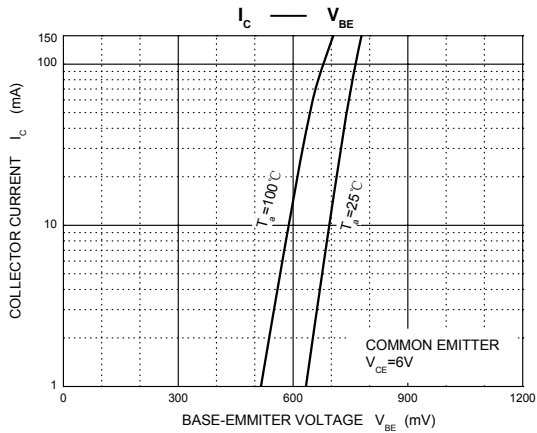
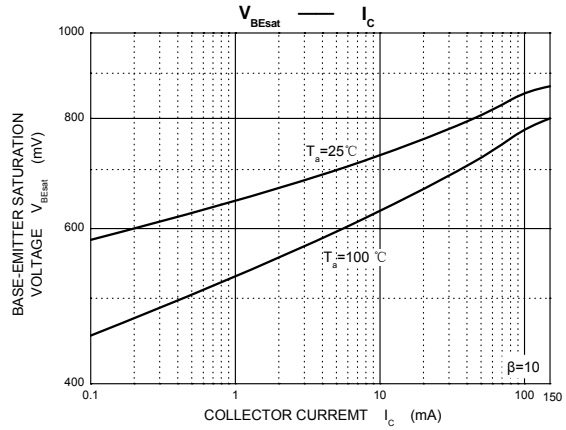
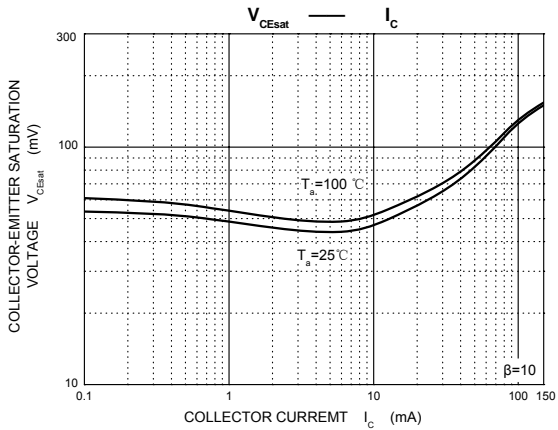
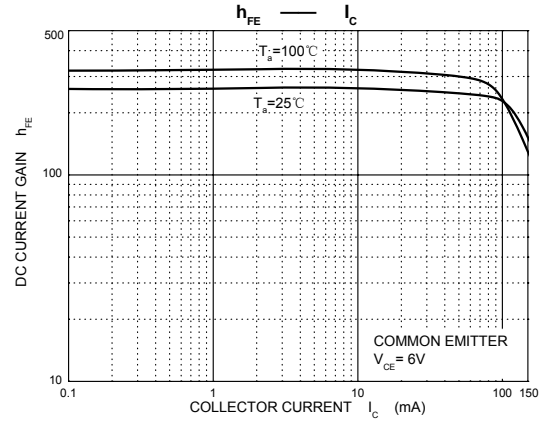
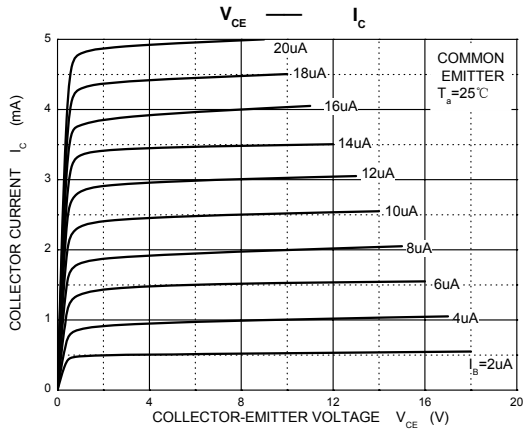
CHINA BASE
INTERNATIONAL

SOT-563

EMX1

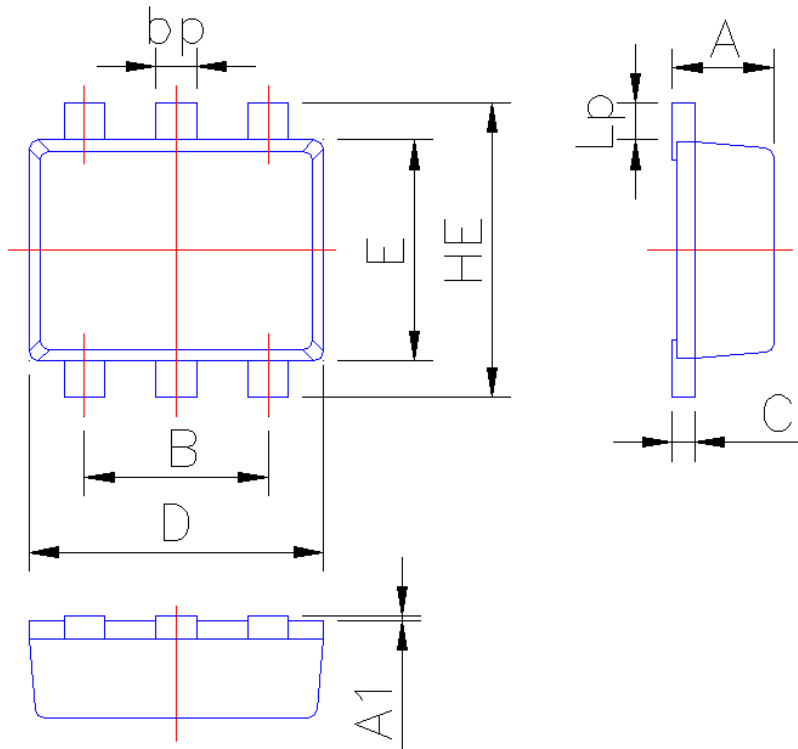


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SOT-563-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.50	0.60
A1	0	0.05
B	0.95	1.05
bp	0.13	0.30
C	0.09	0.150
D	1.50	1.70
E	1.15	1.35
HE	1.40	1.80
Lp	0.13	0.30